Application No.: 10/697,024 Docket No. 8733.895.00-US

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

- 1. (Withdrawn) An array substrate for a liquid crystal display device, comprising:
- a substrate having a non-display region and a display region;
- a plurality of gate and data lines crossing each other on the substrate;
- a gate electrode connected to one of said gate lines;
- a gate insulating layer on the gate line and the gate electrode;
- an active layer on the gate insulating layer over the gate electrode;
- an ohmic contact layer on the active layer;
- source and drain electrodes spaced apart from each other on the ohmic contact layer;
- a pixel electrode connected to the drain electrode and contacting the gate insulating layer; an alignment layer on the pixel electrode;
- gate and data pads defined as an end portion of the gate and data lines, respectively, said gate and data pads positioned at the non-display region; and

gate and data pad terminals on the gate and data pads, respectively.

- 2. (Withdrawn) The array substrate according to claim 1, wherein the data pad terminal extends to the display region.
- 3. (Withdrawn) The array substrate according to claim 1, wherein a data pad terminal comprises the same material as the pixel electrode.
- 4. (Withdrawn) The array substrate according to claim 1, wherein the alignment layer comprises polyimide.

Application No.: 10/697,024 Docket No. 8733.895.00-US

5-17. (Cancelled)

18. (Previously Presented) A method of manufacturing an array substrate for a liquid crystal display device comprising:

forming a thin film transistor having a gate electrode, source and drain electrodes, an active layer, and an ohmic contact layer;

forming a pixel electrode contacting the drain electrode,

wherein the formation of at least one of the electrodes, the active layer, and the ohmic contact layer are processed by a photolithography method using photoresists,

wherein the ohmic contact layer is etched by a dry etching process in a chamber, and wherein a photoresist used in the formation of the ohmic contact layer is removed by a dry strip method using dry gases in the chamber and wherein an upper surface of the ohmic contact layer is etched after the dry strip method.

- 19. (Original) The method according to claim 18, wherein the dry gases used in the dry strip include O_2 as a base gas and SF_6 or CF_4 as a reactive gas.
 - 20. (Cancelled).
- 21. (Previously Presented) The method according to claim 18, wherein the upper surface of the ohmic contact layer is etched to a depth of between 100 and 700 Angstroms.
- 22. (Original) The method according to claim 21, wherein a thickness of the ohmic contact layer before etching is between about 400 and about 1,000 Angstroms.
 - 23. (Withdrawn) A liquid crystal display device, comprising:
 - a gate electrode on a substrate having a display region and a non-display region;
 - a gate insulating layer on the gate electrode;
- an active layer and an ohmic contact layer on the gate insulating layer over the gate electrode;

Docket No. 8733.895.00-US

Application No.: 10/697,024

source and drain electrodes;

- a pixel electrode contacting the drain electrode on the gate insulating layer; an alignment layer on the pixel electrode and the source and drain electrodes;
- a data line connected to the source electrode and having a data pad at the non-display region; and
- a data pad terminal directly contacting the data pad and contacting and extending below a seal pattern between two substrates.